# BC182, BC182B

# **Amplifier Transistors**

# **NPN Silicon**

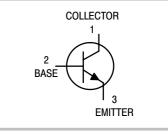
### Features

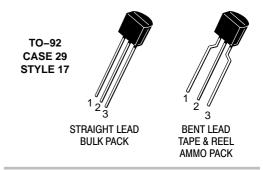
• These are Pb–Free Devices\*



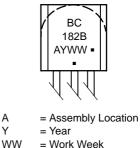
## **ON Semiconductor®**

http://onsemi.com





### MARKING DIAGRAM



= Work Week

А

V

= Pb-Free Package

(Note: Microdot may be in either location)

### **ORDERING INFORMATION**

Device	Package	Shipping <sup>†</sup>
BC182G	TO–92 (Pb–Free)	5000 Units / Bulk
BC182BG	TO-92 (Pb-Free)	5000 Units / Bulk
BC182BRL1G	TO–92 (Pb–Free)	2000 / Tape & Reel

+For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

\*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

## MAXIMUM RATINGS

Rating	Symbol	Value	Unit	
Collector-Emitter Voltage	V <sub>CEO</sub>	50	Vdc	
Collector-Base Voltage	V <sub>CBO</sub>	60	Vdc	
Emitter-Base Voltage	V <sub>EBO</sub>	6.0	Vdc	
Collector Current – Continuous	Ι <sub>C</sub>	100	mAdc	
Total Device Dissipation @ $T_A = 25^{\circ}C$ Derate above 25°C	PD	350 2.8	mW mW/°C	
Total Device Dissipation @ $T_C = 25^{\circ}C$ Derate above 25°C	PD	1.0 8.0	W mW/°C	
Operating and Storage Junction Temperature Range	T <sub>J</sub> , T <sub>stg</sub>	-55 to +150	°C	

## THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit	
Thermal Resistance, Junction-to-Ambient	$R_{\thetaJA}$	357	°C/W	
Thermal Resistance, Junction-to-Case	$R_{\theta JC}$	125	°C/W	

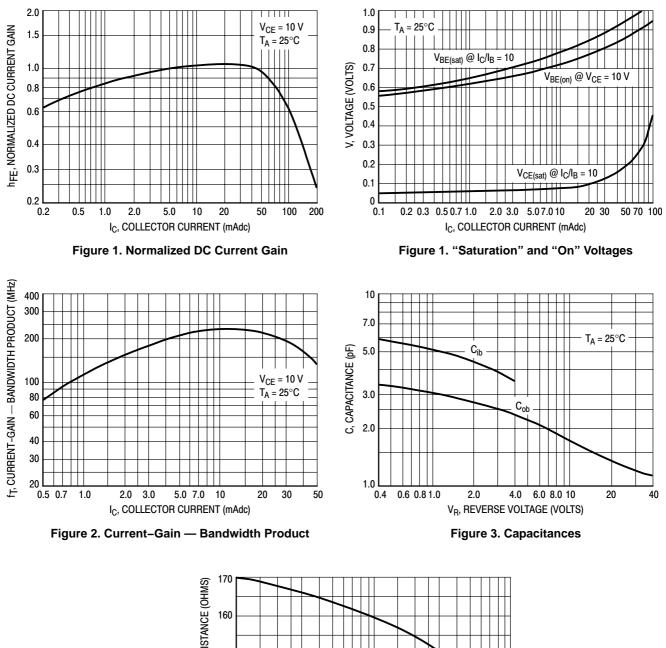
Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

# BC182, BC182B

## **ELECTRICAL CHARACTERISTICS** (T<sub>A</sub> = 25°C unless otherwise noted)

Characteristic		Symbol	Min	Тур	Max	Unit
OFF CHARACTERISTICS	·					
Collector – Emitter Breakdown Voltage $(I_{C} = 2.0 \text{ mA}, I_{B} = 0)$		V <sub>(BR)CEO</sub>	50	-	_	V
Collector–Base Breakdown Voltage $(I_{C} = 10 \ \mu A, I_{E} = 0)$		V <sub>(BR)CBO</sub>	60	-	_	V
Emitter – Base Breakdown Voltage $(I_E = 100 \ \mu\text{A}, I_C = 0)$		V <sub>(BR)EBO</sub>	6.0	-	_	V
Collector Cutoff Current $(V_{CB} = 50 \text{ V}, V_{BE} = 0)$		I <sub>CBO</sub>	_	0.2	15	nA
Emitter–Base Leakage Current $(V_{EB} = 4.0 \text{ V}, I_C = 0)$		I <sub>EBO</sub>	-	-	15	nA
ON CHARACTERISTICS						
DC Current Gain $(I_C = 10 \ \mu\text{A}, \ V_{CE} = 5.0 \ \text{V})$	BC182	h <sub>FE</sub>	40	-	_	-
$(I_{C} = 2.0 \text{ mA}, V_{CE} = 5.0 \text{ V})$	BC182 BC182B		120 180		500 500	
(I <sub>C</sub> = 100 mA, V <sub>CE</sub> = 5.0 V)	BC182		80	-	_	
Collector – Emitter On Voltage ( $I_c = 10 \text{ mA}, I_B = 0.5 \text{ mA}$ ) ( $I_c = 100 \text{ mA}, I_B = 5.0 \text{ mA}$ ) (Note 1)		V <sub>CE(sat)</sub>		0.07 0.2	0.25 0.6	V
Base – Emitter Saturation Voltage (I <sub>C</sub> = 100 mA, I <sub>B</sub> = 5.0 mA) (Note 1)		V <sub>BE(sat)</sub>	-	-	1.2	V
Base-Emitter On Voltage $(I_C = 100 \ \mu\text{A}, V_{CE} = 5.0 \ \text{V})$ $(I_C = 2.0 \ \text{mA}, V_{CE} = 5.0 \ \text{V})$ $(I_C = 100 \ \text{mA}, V_{CE} = 5.0 \ \text{V})$ (Note 1)		V <sub>BE(on)</sub>	 0.55 	0.5 0.62 0.83	_ 0.7 _	V
DYNAMIC CHARACTERISTICS						
Current-Gain — Bandwidth Product ( $I_C = 0.5 \text{ mA}, V_{CE} = 3.0 \text{ V}, f = 100 \text{ MHz}$ ) ( $I_C = 10 \text{ mA}, V_{CE} = 5.0 \text{ V}, f = 100 \text{ MHz}$ )		f <sub>T</sub>	_ 150	100 200		MHz
Common Base Output Capacitance $(V_{CB} = 10 \text{ V}, I_C = 0, f = 1.0 \text{ MHz})$		C <sub>ob</sub>	-	-	5.0	pF
Common Base Input Capacitance $(V_{EB} = 0.5 \text{ V}, I_C = 0, f = 1.0 \text{ MHz})$		C <sub>ib</sub>	_	8.0	_	pF
Small–Signal Current Gain ( $I_C = 2.0 \text{ mA}, V_{CE} = 5.0 \text{ V}, f = 1.0 \text{ kHz}$ )	BC182 BC182B	h <sub>fe</sub>	125 240		500 500	-
Noise Figure (I <sub>C</sub> = 0.2 mA, V <sub>CE</sub> = 5.0 V, R <sub>S</sub> = 2.0 k $\Omega$ , f = 1.0 kHz)		NF	_	2.0	10	dB

1. Pulse Test: Tp 300 s, Duty Cycle 2.0%.



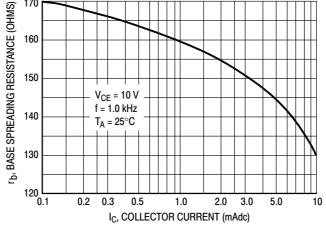
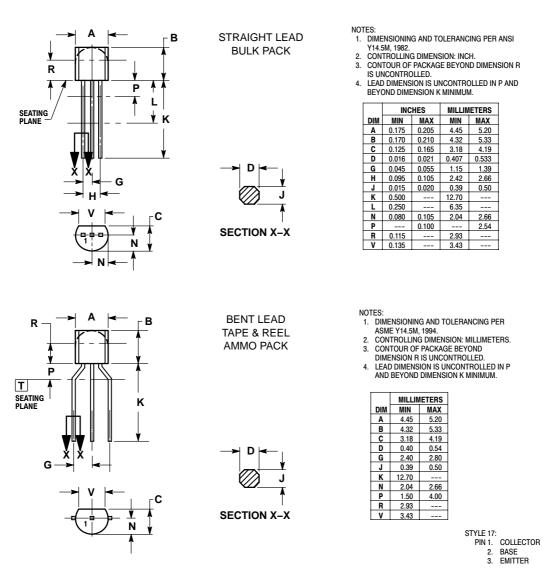


Figure 4. Base Spreading Resistance

#### PACKAGE DIMENSIONS

TO-92 (TO-226) CASE 29-11 ISSUE AM



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